

FEATURES

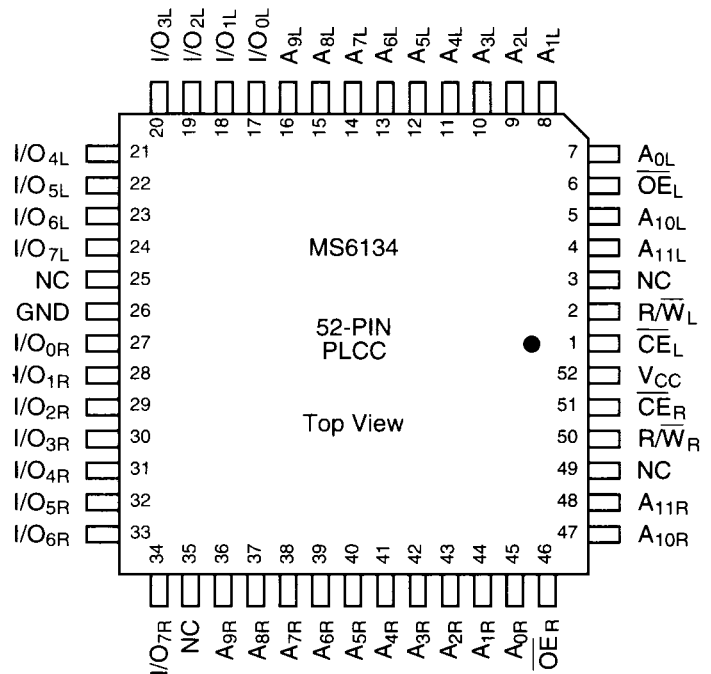
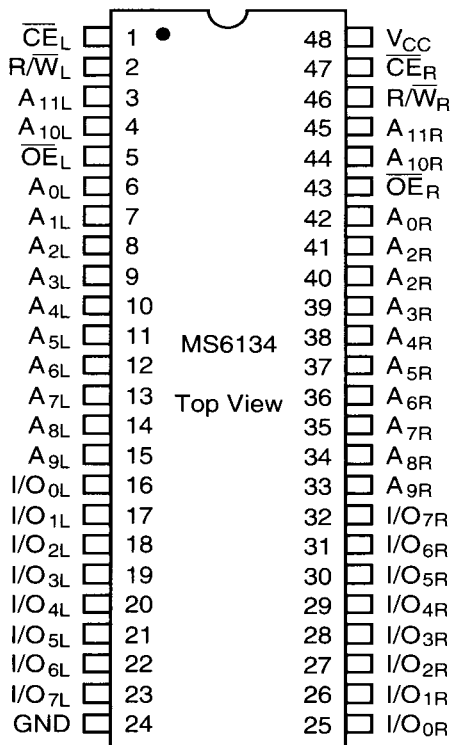
- High-speed – 45/55/70 ns
- MS6134 — Standalone device
- True Dual Port Memory array
- Low Power dissipation
325mW (Typ.) Operating
5mW (Typ.) Standby
- Fully static operation
- All inputs and outputs directly TTL compatible
- Three state outputs
- Data retention supply voltage: 2.0-5.5V
- Fully asynchronous operation from either port

DESCRIPTION

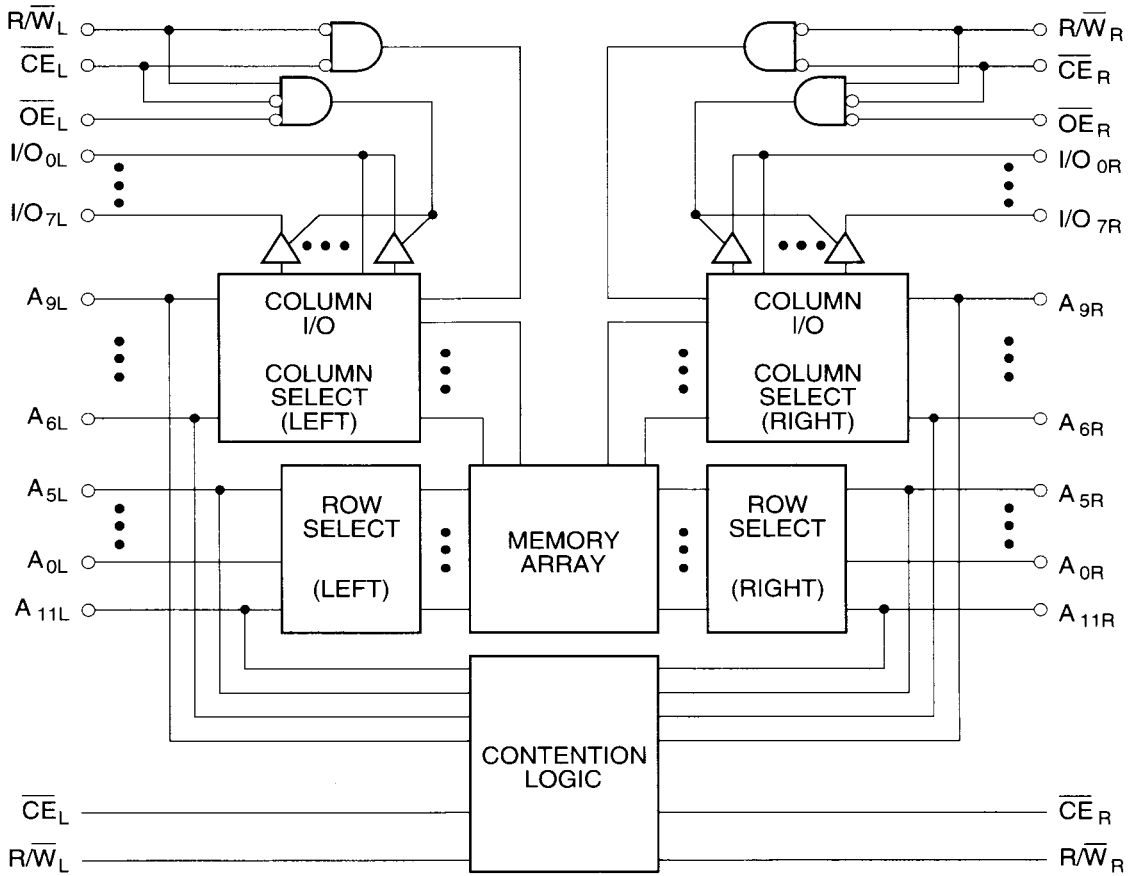
The MOSEL MS6134 is a 32,768 bit dual port static random access memory organized as 4,096 words by 8 bits allowing each port to independently access any location in memory. The MS6134 is ideal for systems that require no on-chip arbitration.

Systems using the MS6134 must be capable of withstanding or provide on external solutions in order to prevent contention, either an on-chip arbiter or software. Power reduction circuitry offers a battery backup data retention capability where the circuit typically consumes only 200µW off a 2V battery. The MS6134 is packaged in a 48-pin 600 mil-DIP, and 52-pin PLCC.

PIN CONFIGURATIONS



FUNCTIONAL BLOCK DIAGRAM



MS6134

PIN DESCRIPTIONS

LEFT PORT	RIGHT PORT	NAMES
\overline{CE}_L	\overline{CE}_R	CHIP ENABLE
R/\overline{W}_L	R/\overline{W}_R	READ/WRITE ENABLE
\overline{OE}_L	\overline{OE}_R	OUTPUT ENABLE
$A_{0L}-A_{11L}$	$A_{0R}-A_{11R}$	ADDRESS
$I/O_{0L}-I/O_{7L}$	$I/O_{0R}-I/O_{7R}$	DATA INPUT/OUTPUT
V_{CC}		POWER
GND		GROUND

FUNCTIONAL DESCRIPTION

The MS6134 provides two ports with separate controls, address and I/O that permit independent access for reads or writes to any location in memory. The MS6134 has an automatic power-down feature controlled by \overline{CE} . The \overline{CE} controls on-chip power-down circuitry that permits the respective port to go into a standby mode when not selected (\overline{CE} high). When a port is enabled, access to the entire memory array is permitted. Each port has its own Output Enable control (\overline{OE}). In the read mode, \overline{OE} enables the output drivers when set LOW. Non-contention READ/WRITE conditions are illustrated in truth table.

TRUTH TABLE

LEFT PORT INPUTS			RIGHT PORT INPUT			FUNCTION
R/\overline{W}_L	\overline{CE}_L	\overline{OE}_L	R/\overline{W}_R	\overline{CE}_R	\overline{OE}_R	
X	H	X	X	X	X	Left Port in Power Down Mode
X	X	X	X	H	X	Right Port in Power Down Mode
L	L	X	X	X	X	Data on Left Port Written Into Memory
H	L	L	X	X	X	Data in Memory Output on Left Port
X	X	X	L	L	X	Data on Right Port Written Into Memory
X	X	X	H	L	L	Data in Memory Output on Right Port

ABSOLUTE MAXIMUM RATINGS ⁽¹⁾

PARAMETER NAME	PARAMETER	CONDITION	UNIT
V_{TERM}	Terminal Voltage with Respect to GND	-0.5 to +7.0	V
T_{BIAS}	Temperature Under Bias	-55 to +125	°C
T_{STG}	Storage Temperature	-55 to +150	°C
P_T	Power Dissipation	1.0	W
I_{OUT}	DC Output Current	20	mA

NOTE:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

OPERATING RANGE

RANGE	AMBIENT TEMPERATURE	V_{CC}
Commercial	0°C to +70°C	5V ± 10%

DC ELECTRICAL CHARACTERISTICS ($V_{CC} = 5V \pm 10\%$, $T_A = 0^\circ\text{C}$ to $+70^\circ\text{C}$)

PARAMETER NAME	PARAMETER	TEST CONDITIONS	MS6134			UNIT
			MIN.	TYP. (1)	MAX.	
I_{LH}	Input Leakage Current	$V_{CC} = 5.5V$, $V_{IN} = 0V$ to V_{CC}	—	—	2	μA
I_{LO}	Output Leakage Current	$\overline{CE} = V_{IH}$, $V_{OUT} = 0V$ to V_{CC}	—	—	2	μA
V_{IH}	Input High Voltage		2.2		6.0	V
V_{IL}	Input Low Voltage		-0.5		0.8	V
I_{CC}	Dynamic Operating Current (Both Ports Active)	$\overline{CE} = V_{IL}$, Output open, $t_{RC} = 45\text{ns}$ $t_{RC} = 55\text{ns}$ $t_{RC} = 70\text{ns}$	—	—	190 180 180	mA
I_{SB1}	Standby Current (Both Ports Standby)	\overline{CE}_L and $\overline{CE}_R \geq V_{IH}$	—	25	40	mA
I_{SB2}	Standby Current (One Port Standby)	\overline{CE}_L or $\overline{CE}_R \geq V_{IH}$ Active Port Outputs Open	—	40	120	mA
I_{SB3}	Full Standby Current (Both Ports Full Standby)	Both Ports \overline{CE}_L and $\overline{CE}_R \geq V_{CC} - 0.2V$ $V_{IN} \geq V_{CC} - 0.2V$ to $V_{IN} \leq 0.2V$	—	1	5	mA
I_{SB4}	Full Standby Current (One Port Full Standby)	One Ports \overline{CE}_L or $\overline{CE}_R \geq V_{CC} - 0.2V$ $V_{IN} \geq V_{CC} - 0.2V$ to $V_{IN} \leq 0.2V$ Active Port Outputs Open	—	—	105	mA
V_{OL}	Output Low Voltage ($I_{O0} - I_{O7}$)	$I_{OL} = 8\text{mA}$	—	—	0.4	V
V_{OH}	Output High Voltage	$I_{OH} = -4\text{mA}$	2.4	—	—	V

NOTE:

1. $V_{CC} = 5V \pm 10\%$, $T_A = 0^\circ\text{C}$ to $+70^\circ\text{C}$.

CAPACITANCE⁽¹⁾ ($T_A = 25^\circ\text{C}$, $f = 1.0\text{MHz}$)

PARAMETER NAME	PARAMETER	CONDITIONS	MAX.	UNIT
C_{IN}	Input Capacitance	$V_{IN} = 0V$	15	pF
C_{OUT}	Output Capacitance	$V_{OUT} = 0V$	15	pF

NOTE:

1. This parameter is guaranteed and not 100% tested.

MS6134

AC ELECTRICAL CHARACTERISTICS ($V_{CC} = 5V \pm 10\%$, $T_A = 0^\circ C$ to $+70^\circ C$)

PARAMETER NAME	PARAMETER	MS6134-45		MS6134-55		MS6134-70		UNITS
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
READ CYCLE								
t_{RC}	Read Cycle Time	45	—	55	—	70	—	ns
t_{AA}	Address Access Time	—	45	—	55	—	70	ns
t_{ACE}	Chip Enable Access Time	—	45	—	55	—	70	ns
t_{AOE}	Output Enable Access Time	—	20	—	30	—	35	ns
t_{OH}	Output Hold from Address Change	3	—	5	—	5	—	ns
t_{LZ}	Output Low Z Time ^{(1), (2)}	3	—	5	—	5	—	ns
t_{HZ}	Output High Z Time ^{(1), (2)}	—	20	—	30	—	35	ns
t_{PU}	Chip Enable to Power Up Time ⁽²⁾	0	—	0	—	0	—	ns
t_{PD}	Chip Disable to Power Down Time ⁽²⁾	—	25	—	40	—	45	ns
WRITE CYCLE								
t_{WC}	Write Cycle Time	45	—	55	—	70	—	ns
t_{EW}	Chip Enable to End of Write	35	—	40	—	45	—	ns
t_{AW}	Address Valid to End of Write	35	—	40	—	45	—	ns
t_{AS}	Address Setup Time	0	—	0	—	0	—	ns
t_{WP}	Write Pulse Width	35	—	40	—	45	—	ns
t_{WR}	Write Recovery Time	0	—	0	—	0	—	ns
t_{DS}	Input Data Setup Time	25	—	30	—	30	—	ns
t_{DH}	Data Hold Time	0	—	0	—	0	—	ns
t_{WZ}	Write Enabled to Output in High-Z ^{(1), (2)}	0	20	0	25	0	30	ns
t_{OW}	Output Active From End of Write ^{(1), (2)}	3	—	3	—	3	—	ns

NOTES:

1. Transition is measured $\pm 500mV$ from low or high impedance voltage with load (Figures 1, 2 and 3).
2. This parameter is guaranteed but not tested.

AC TEST CONDITIONS

Input Pulse Levels	GND to 3.0V
Input Rise and Fall Times	5ns
Input and Output Timing Reference Levels	1.5V
Output Load	See Figure 1 and 2

* Including scope and jig.

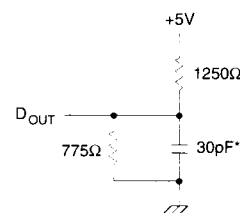


Figure 1
Output Load

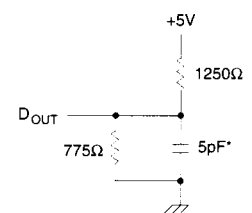
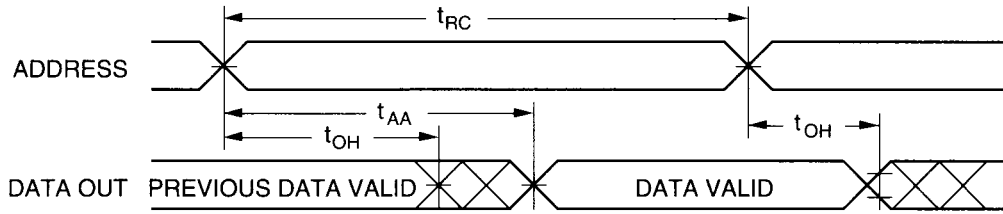


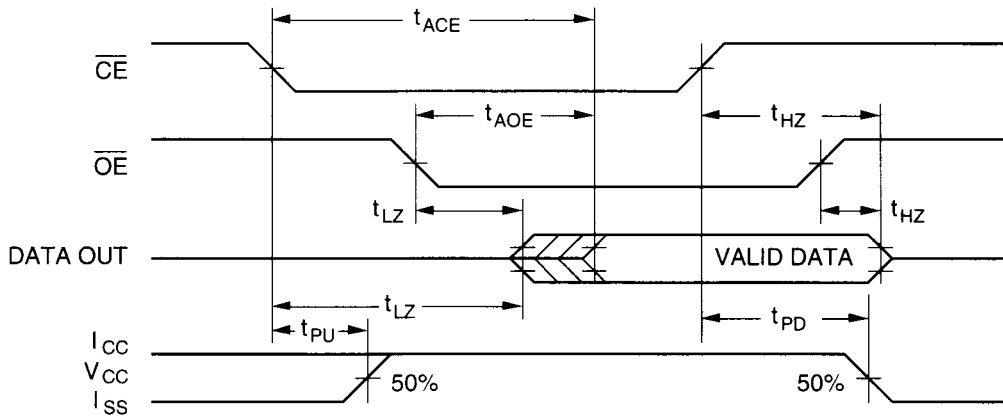
Figure 2
Output Load
(for t_{HZ} , t_{LZ} , t_{WZ} , and t_{OW})

TIMING WAVEFORMS

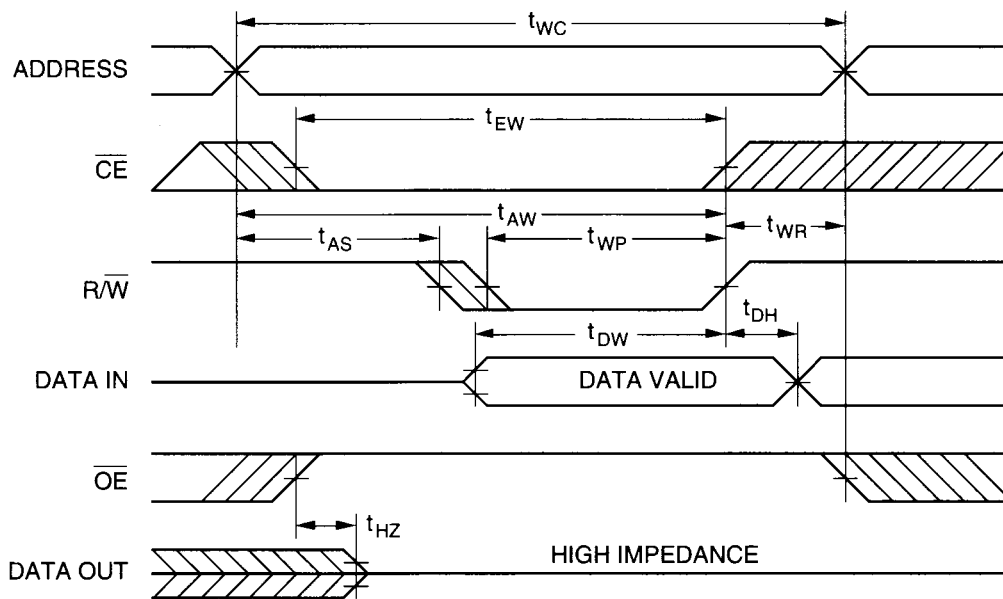
READ CYCLE NO. 1 EITHER SIDE (1), (2), (6)



READ CYCLE NO. 2 EITHER SIDE (1), (3)



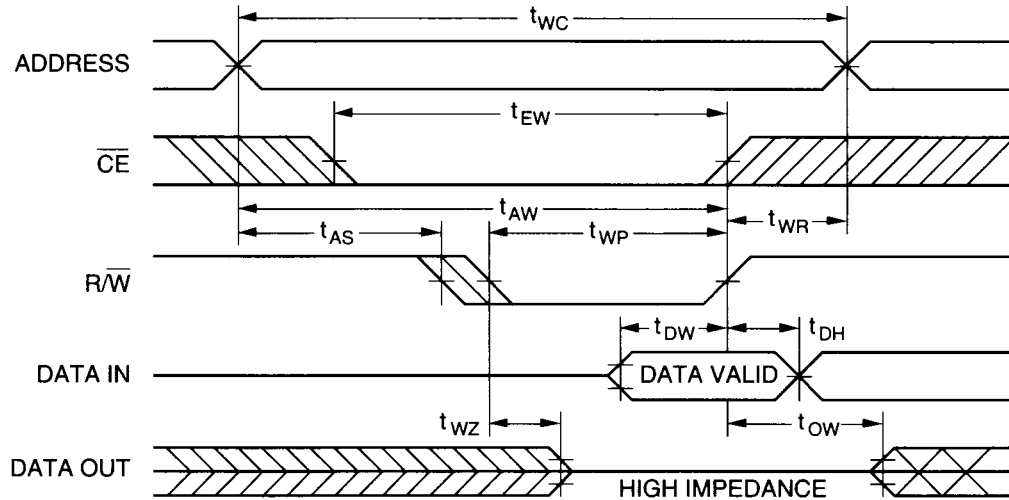
WRITE CYCLE NO. 1 EITHER SIDE (4), (7)



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TIMING WAVEFORMS

WRITE CYCLE NO. 2 EITHER SIDE (4), (7)



NOTES:

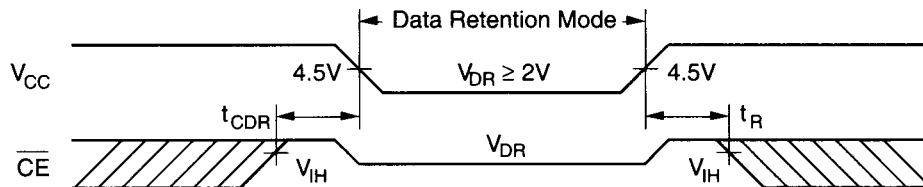
1. $\overline{R/W}$ is high for Read Cycles.
2. Device is continuously enabled, $\overline{CE} = V_{IL}$.
3. Addresses valid prior to coincident with \overline{CE} transition low.
4. If \overline{CE} goes high simultaneously with $\overline{R/W}$ high, the outputs remain in the high impedance state.
5. $\overline{CE}_L = \overline{CE}_R = V_{IL}$.
6. $\overline{OE} = V_{IL}$.
7. $\overline{R/W} = V_{IH}$ during address transition.

DATA RETENTION CHARACTERISTICS ($T_A = 0^\circ\text{C}$ to $+70^\circ\text{C}$)

PARAMETER NAME	PARAMETER	TEST CONDITIONS	MIN.	TYP.(1)	MAX.	UNIT
V_{DR}	V_{CC} for Data Retention		2.0	—	—	V
I_{CCDR}	Data Retention Current	$V_{CC} = 2.0\text{V}$	—	—	500	μA
t_{CDR}	Chip Deselect to Data Retention Time	$CS \geq V_{CC} - 0.2\text{V}$	0	—	—	ns
t_R	Operation Recovery Time	$V_{IN} \geq V_{CC} - 0.2\text{V}$ or $\leq 0.2\text{V}$	$t_{RC}^{(2)}$	—	—	ns

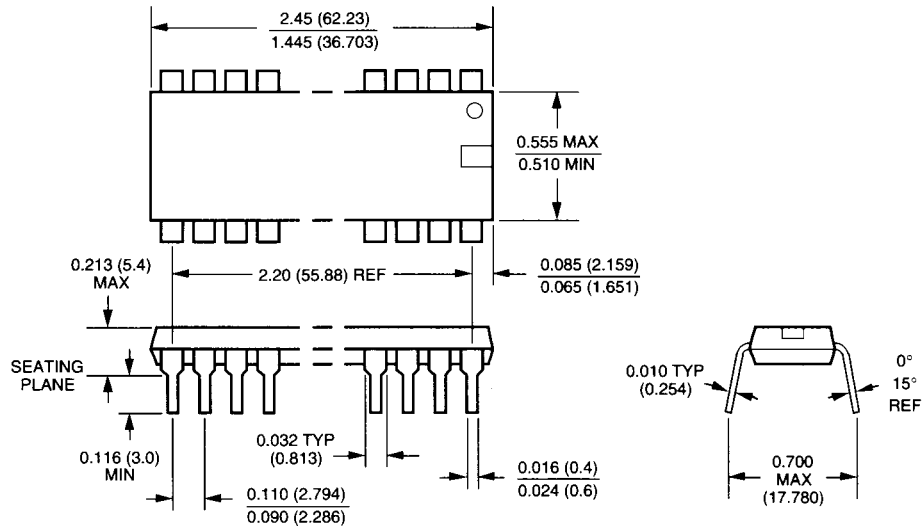
NOTES:

1. $T_A = +25^\circ\text{C}$.
2. t_{RC} = Read Cycle Time.

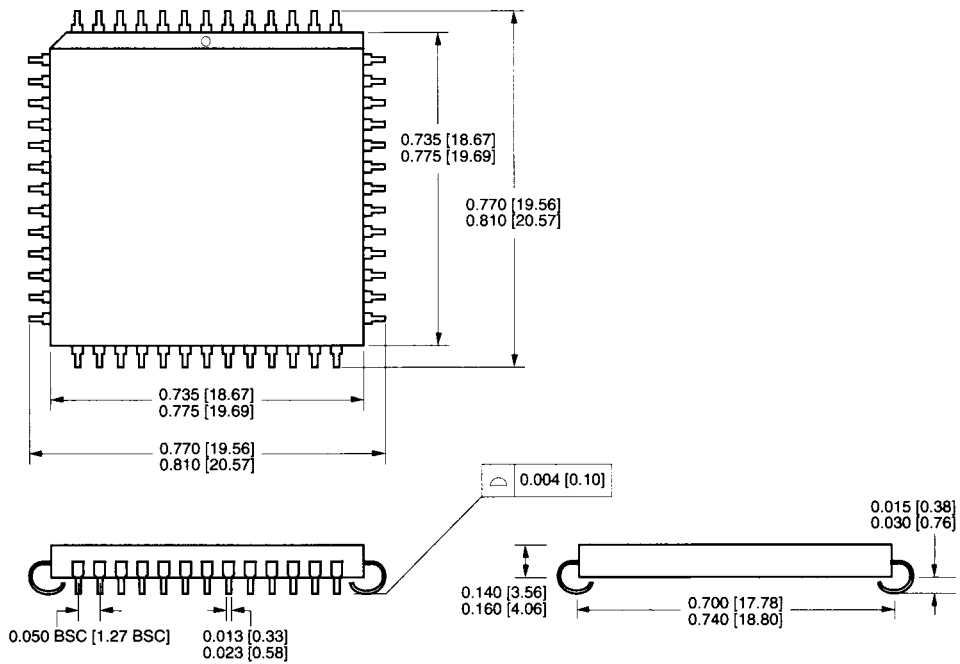


PACKAGE DIAGRAM

48-Pin Plastic Dual In-Line Package (P48-2)



52-Pin PLCC Package (J52-1)



DIMENSIONS IN INCHES [MM]

MS6134

ORDERING INFORMATION

SPEED (ns)	ORDERING PART NUMBER	PACKAGE	TEMPERATURE RANGE (1)
45	MS6134-45PC	Plastic DIP - 600 mil	0°C to +70°C
55	MS6134-55PC	Plastic DIP - 600 mil	0°C to +70°C
70	MS6134-70PC	Plastic DIP - 600 mil	0°C to +70°C
45	MS6134-45JC	52-Pin PLCC	0°C to +70°C
55	MS6134-55JC	52-Pin PLCC	0°C to +70°C
70	MS6134-70JC	52-Pin PLCC	0°C to +70°C

NOTE:

1. Contact MOSEL-VITELIC Marketing for -40°C to +85°C Industrial Temperature.